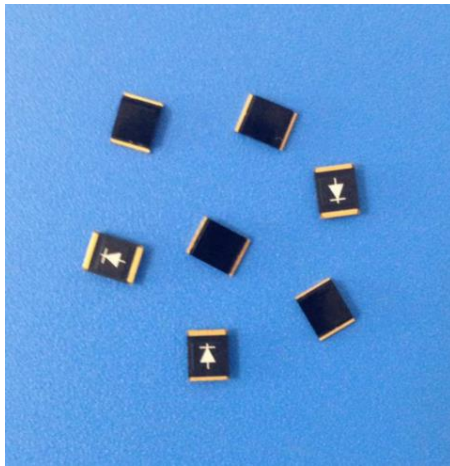


Visible light cut photodiode



Description

The OSD9-AM is device as visible cut, IR wavelength PD in COB package, It can get fast response output of high Sensitivity for IR light. This device is ideal for applications Such as optical switch etc.

Features

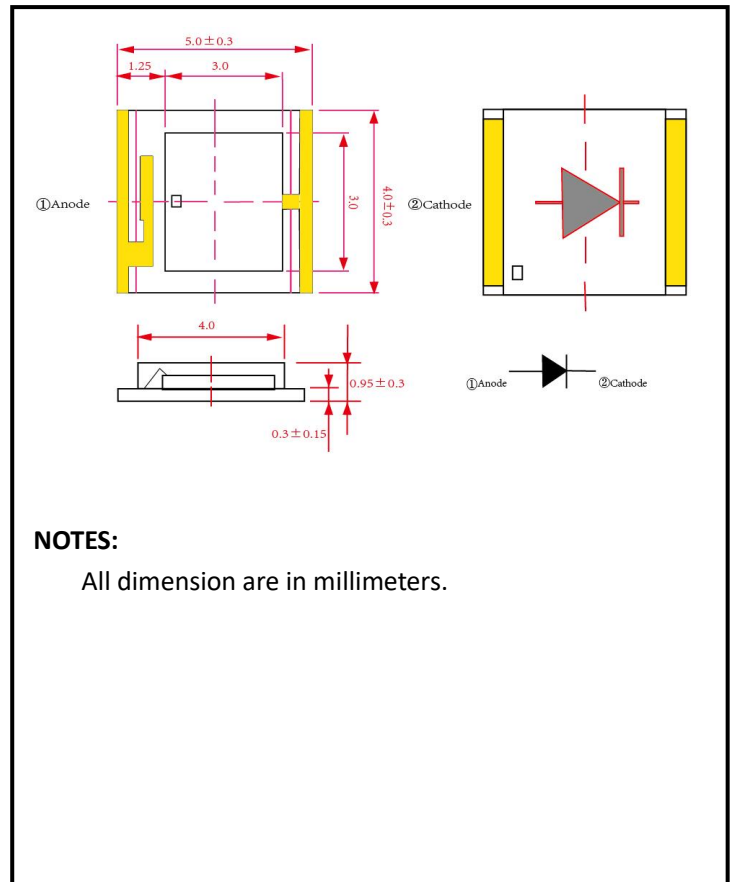
- * high sensitivity for IR light.
- * Low dark current
- * Daylight filter
- * Operating temperature is from -40 to $+80^{\circ}\text{C}$
- * Storage temperature is from -40 to $+100^{\circ}\text{C}$

General Ratings

- * peak wavelength: 940nm
- * Low capacitance

Applications

- *Optical switch
- *Optical module
- *IR sensor



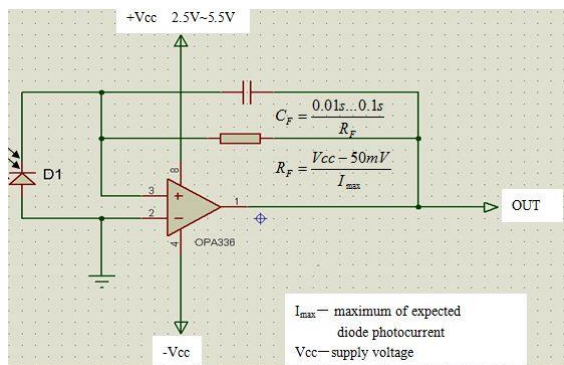
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Absolute Maximum Ratings (Ta=25 °C)

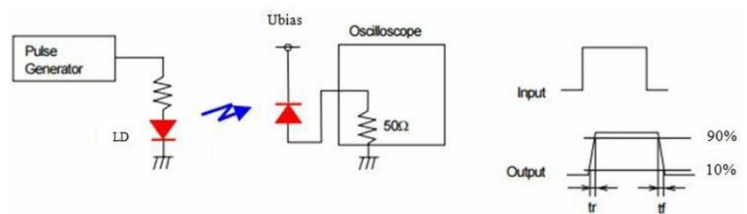
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	Size			3.0*3.0		mm ²
Active area	A			2.84*2.84		mm ²
Short circuit Current	I _{sc}	V _r =5V, E _v =1000lux f _c =2856k*		57		μA
Isc Temperature Coefficient	TC I _{sc}	2856k		1.1		%/°C
Open Circuit Voltage	V _{oc}	V _r =5V, E _v =1000lux f _c =2856k*		320		mV
Voc Temperature Coefficient	TC Voc	2856k		-2.2		mV/°C
Dark current	I _d	V _R =100mV		15		pA
		V _R =10V		1000		
Rise time	t _{r**}	V _R =0V; λ=635nm; R _L =50Ω, f=1KHz		100		ns
		V _R =10V; λ=635nm; R _L =50Ω, f=1KHz		80		ns
Temp coefficient of I _d	T _{CI_d}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100μA E _v =0lx	30			V
Junction Capacitance	C _J	V _R =0V f=1MHz		70		pF
		V _R =10V f=1MHz		25		
Photo sensitivity	S _R	940nm		0.64		A/W
Spectral Application Range	λ _{range}		750		1100	nm
Spectral Response-Peak	λ _p			940		nm
Shunt resistance	R _{sh}	V _R =10mV		0.5		GΩ
Rsh Temperature Coefficient	TC R _{sh}	E _v =100lx, V _R =10mV		0.18		%/°C
Angular Resp 50% Resp Pt	θ _{1/2}			±60		Degrees
Noise Equivalent Power	NEP	V _R =10V λ=940nm		2.58*10 ⁻¹⁴		W/Hz ^{1/2}
Specific Detectivity	D*	V _R =10V λ=940nm		1.67*10 ¹³		cm(Hz/W) ^{1/2}

* E_v: Illuminance by CIE standard light source A (tungsten lamp)

■ Typical application circuit



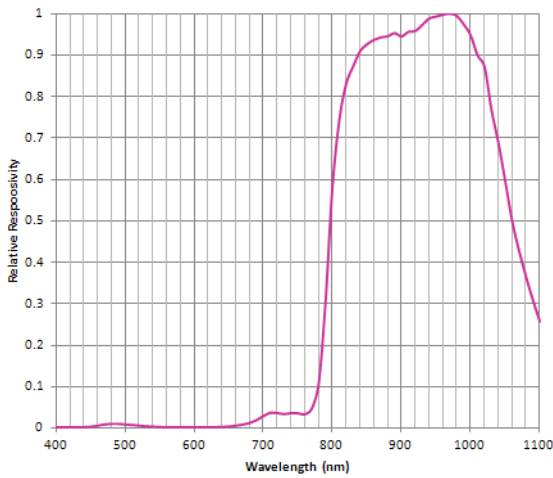
** Response time measurement Circuit:



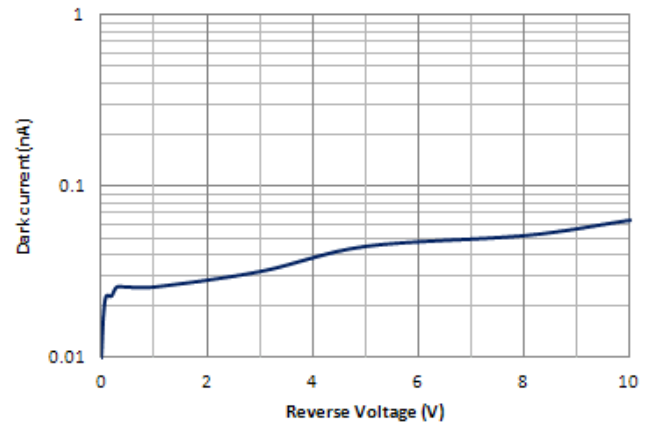
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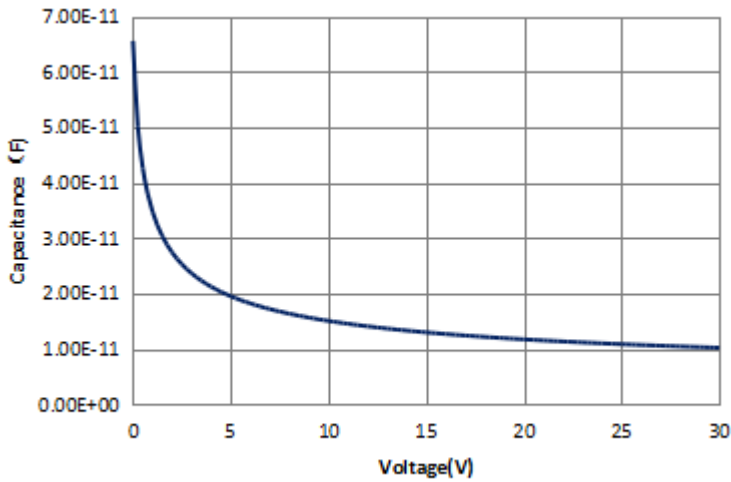
SPECTRAL RESPONSE (Ta=23°C)



DARK CURRENT VS. REVERSE VOLTAGE (Ta=23°C)



CAPACITANCE VS. REVERSE VOLTAGE (Ta=23°C)



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